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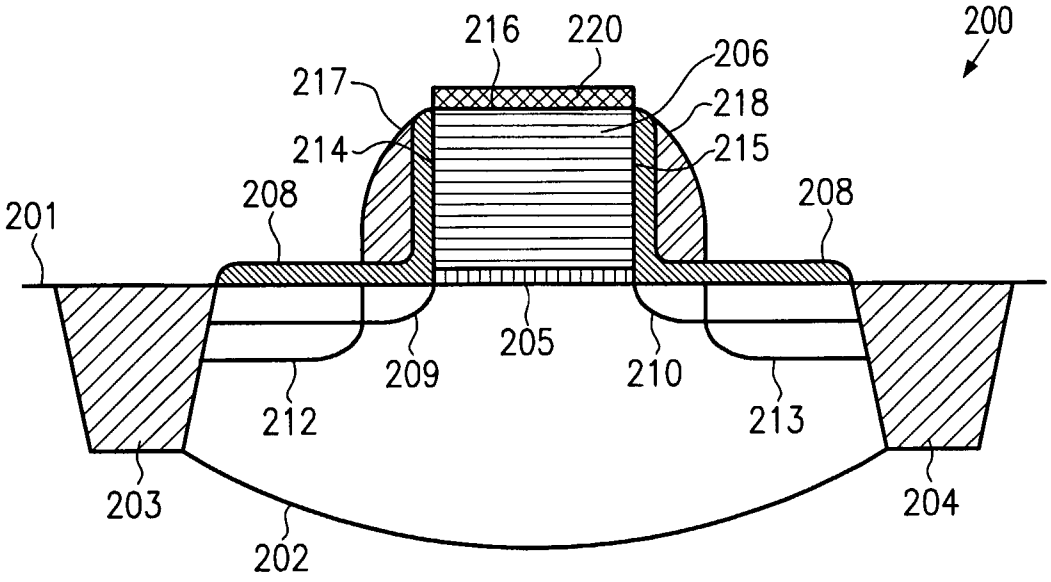
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(54) Title: METHOD OF FORMING SIDEWALL SPACERS



(57) Abstract: The present invention allows the formation of sidewall spacers (217,218) adjacent a feature (206) on a substrate (201) without there being an undesirable erosion of the feature. The feature (206) is covered by one or more protective layers (220,207). A layer of a spacer material (211) is deposited over the feature (206) and etched anisotropically. An etchant used in the anisotropic etching is adapted to selectively remove the spacer material, whereas the one or more protective layers (220, 207) are substantially not affected by the etchant. Thus, the one or more protective layers (220, 207) protect the feature from being exposed to the etchant.

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